GH05U15J 500mA 15kV 50nS

Ultra-Fast Recovery High Voltage Silicon Rectifier Diodes

INTRODUCE:

HVGT high voltage silicon rectifier diodes is made of high quality glass passivated chip and high reliability epoxy resin sealing structure, and through professional testing equipment inspection qualified after to customers.

FEATURES:

1. High reliability design.
2. High voltage, large current..
3. High frequency, Ultra Fast recovery.
4. Conform to RoHS and SGS.
5. Epoxy resin molded in vacuumHave anticorrosion in the surface.

APPLICATIONS:

1. High voltage multiplier circuit
2. High frequency switching power supply .
3. General purpose high voltage rectifier.
4. Laser power supply medical equipment..

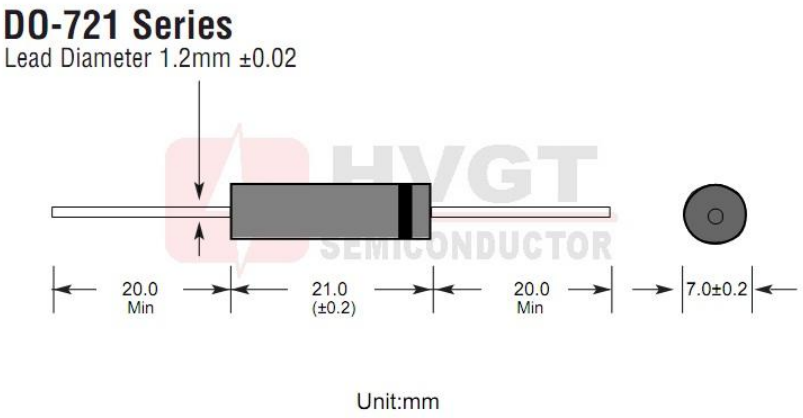
MECHANICAL DATA:

1. Case: epoxy resin molding.
2. Terminal: welding axis.
3. Net weight: 2.10 grams (approx).

SHAPE DISPLAY:



SIZE: (Unit:mm) HVGT NAME: DO-721



MAXIMUM RATINGS AND CHARACTERISTICS: (Absolute Maximum Ratings)

Items	Symbols	Condition	Data Value	Units
Repetitive Peak Renerse Voltage	V_{RRM}	T_A=25°C	15	kV
Non-Repetitive Peak Renerse Voltage	V_{RSM}	T_A=25°C	18	kV
Average Forward Current Maximum	I_{FAVM}	T_A=55°C	500	mA
		T_{OIL}=55°C	600	mA
Non-Repetitive Forward Surge Current	I_{FSM}	T_A=25°C; 60Hz Half-Sine Wave; 8.3mS	20	A
Junction Temperature	T_J		150	°C
Allowable Operation Case Temperature	Tc		-40~+150	°C
Storage Temperature	T_{STG}		-40~+150	°C

ELECTRICAL CHARACTERISTICS: T_A=25°C (Unless Otherwise Specified)

Items	Symbols	Condition	Data value	Units
Maximum Forward Voltage Drop	V_{FM}	at 25°C; at I_{FAVM}	18	V
Maximum Reverse Current	I_{R1}	at 25°C; at V_{RRM}	0.5	uA
	I_{R2}	at 125°C; at V_{RRM}	50	uA
Maximum Reverse Recovery Time	T_{RR}	at 25°C; I_F=0.5I_R; I_R=I_{FAVM}; I_{RR}=0.25I_R	50	nS
Junction Capacitance	C_J	at 25°C; V_R=0V; f=1MHz	3.5	pF

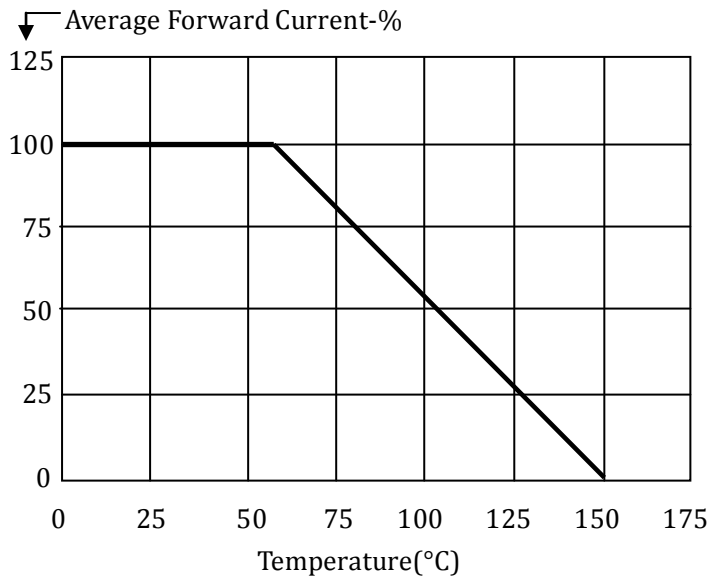
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GH05U15J

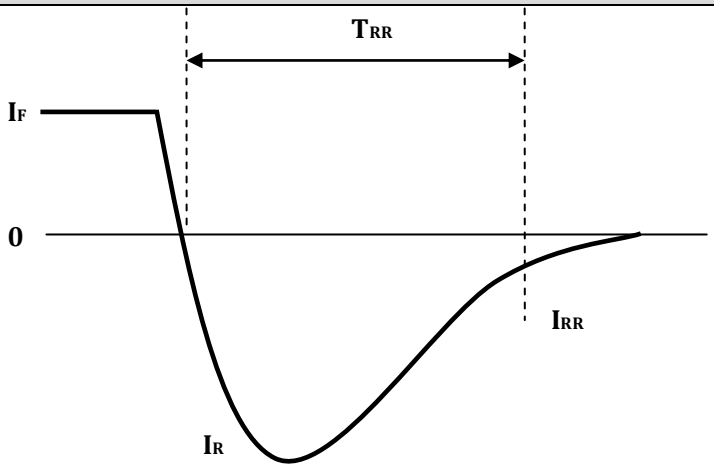
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Forward Current Derating Curve



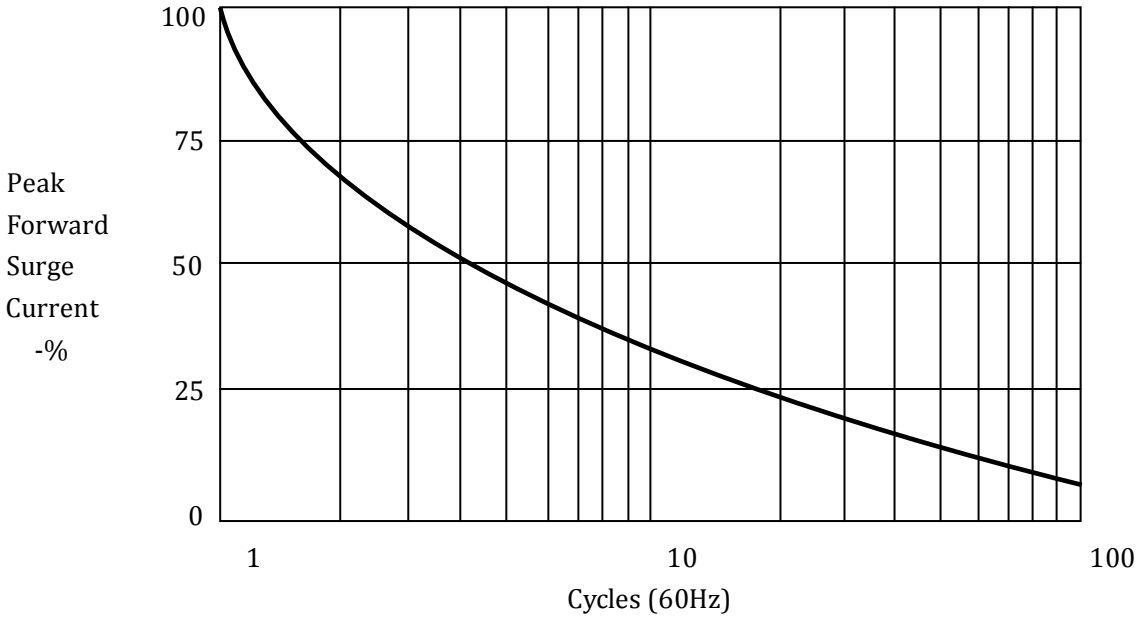
Reverse Recovery Measurement Waveform



Typical data capture points: I_F =0.5I_R , I_R,I_{RR} =0.25I_R

I_R is typically the rated average forward current maximum (I_{FAVM}) of the D.U.T

Non-Repetitive Surge Current



MARKING:

Type	Code	Cathode Mark
GH05U15J	GH05U15J HVGT	

PART NUMBER NOTE:

Chip	Frequency	$I_{F(AV)}$	T_{RR}	V_{RRM}	Dimension Shape Code
G	**H**	**05**	U	**15**	**J**
GPP chip	High Frequency	0.5A	Ultra Fast Recovery	15kV	J=DO-721

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